











TPD4E02B04

SLVSD85B-NOVEMBER 2015-REVISED JULY 2016

TPD4E02B04 4-Channel ESD Protection Diode for USB Type-C and HDMI 2.0

Features

- IEC 61000-4-2 Level 4 ESD Protection
 - ±12-kV Contact Discharge
 - ±15-kV Air Gap Discharge
- IEC 61000-4-4 EFT Protection
 - 80 A (5/50 ns)
- IEC 61000-4-5 Surge Protection
 - 2 A (8/20 µs)
- IO Capacitance:
 - 0.25 pF (Typical)
 - 0.33 pF (Maximum)
- DC Breakdown Voltage: 5.5 V (Minimum)
- Ultra Low Leakage Current: 10 nA (Maximum)
- Low ESD Clamping Voltage: 8.8 V at 5-A TLP
- Supports High Speed Interfaces up to 10 Gbps
- Industrial Temperature Range: -40°C to +125°C
- Easy Flow-Through Routing Package

Applications

- **End Equipment**
 - Laptops and Desktops
 - Set-Top Boxes
 - TV and Monitors
 - Mobile and Tablets
 - DVR and NVR

- Interfaces
 - **USB Type-C**
 - USB 3.1 Gen 2
 - HDMI 2.0/1.4
 - **USB 3.0**
 - DisplayPort 1.3
 - PCI Express 3.0

3 Description

The TPD4E02B04 is a bidirectional TVS ESD protection diode array for USB Type-C and HDMI 2.0 circuit protection. The TPD4E02B04 is rated to dissipate ESD strikes at the maximum level specified in the IEC 61000-4-2 international standard (Level 4).

This device features a 0.25-pF IO capacitance per channel making it ideal for protecting high-speed interfaces up to 10 Gbps such as USB 3.1 Gen2. The low dynamic resistance and low clamping voltage ensure system level protection against transient events.

The TPD4E02B04 is offered in the industry standard USON-10 (DQA) package. The package features flow-through routing and 0.5-mm pin pitch easing implementation and reducing design time.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPD4E02B04	USON (10)	2.50 mm × 1.00 mm

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

Typical Application Schematic

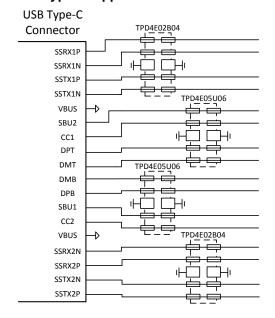




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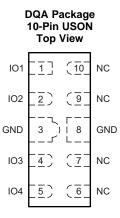
4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	Changes from Revision A (February 2016) to Revision B	Page
•	Updated Capacitance spec in the Features, Description, , IO Capacitance and Operating Frequency sections	1
•	Made changes to Operating Frequency	1
•	Updated Figure 15, Figure 16, Figure 22 and Figure 23	1
С	Changes from Original (Novemeber 2015) to Revision A	Page
•	Changed device status from Product Preview to Production Data	



5 Pin Configuration and Functions



Pin Functions

PIN		TYPE	DESCRIPTION					
NAME	NO.	ITPE	DESCRIPTION					
GND	3	Ground	Ground. Connect to ground					
GND	8	Ground						
IO1	1							
IO2	2	I/O	ECD aretested sharred					
IO3	4	1/0	ESD protected channel					
IO4	5							
NC	6							
NC	7	NC	Not connected; Used for optional straight-through routing. Can be left floating or					
NC 9		INC	grounded					
NC	10							



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Electrical fast transient	IEC 61000-4-5 (5/50 ns)		80	Α
Deal, mules	IEC 61000-4-5 Power (t _p - 8/20 μs)		17	W
Peak pulse	IEC 61000-4-5 Current (t _p - 8/20 μs)		2	Α
T _A	Operating free-air temperature	-40	125	°C
T _{stg}	Storage temperature	-65	155	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

				VALUE	UNIT	
V	V	Floatrootatio displayes	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500		
	V(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 ESD Ratings—IEC Specification

			VALUE	UNIT
V	Electrostatic discharge	IEC 61000-4-2 contact discharge	±12000	V
V(ESD)	Electrostatic discharge	IEC 61000-4-2 air-gap discharge	±15000	V

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{IO}	Input pin voltage	-3.6	3.6	V
T _A	Operating free-air temperature	-40	125	°C

6.5 Thermal Information

		TPD4E02B04	
	THERMAL METRIC ⁽¹⁾	DQA (USON)	UNIT
		10 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	348.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	214.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	270.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	81.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	270.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

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⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

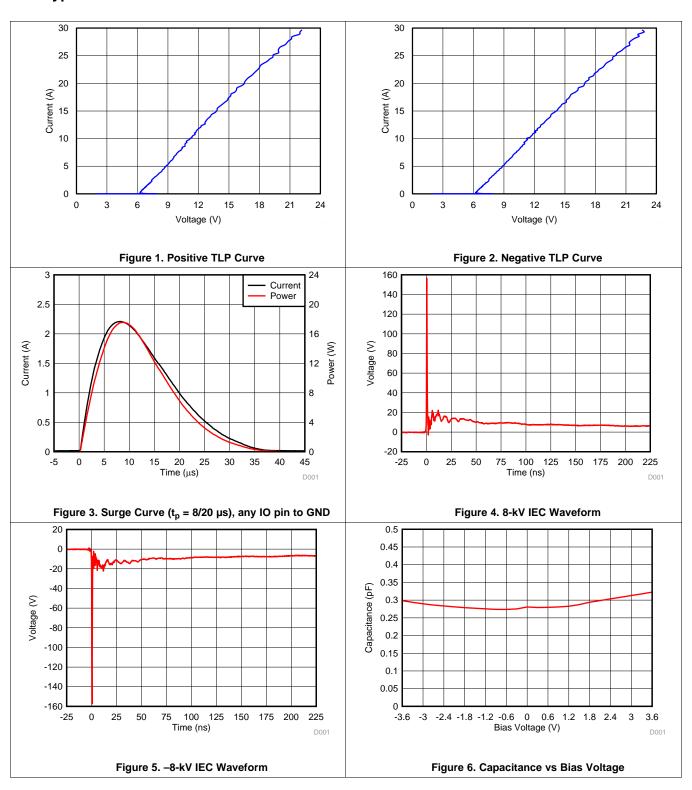
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
V_{RWM}	Reverse stand-off voltage	I _{IO} < 10 nA	-3.6		3.6	٧	
V_{BRF}	Breakdown voltage, any IO pin to GND ⁽¹⁾	I_{IO} = 1 mA, T_A = 25°C	5.5	6.4	7.5	V	
V_{BRR}	Breakdown voltage, GND to any IO pin ⁽¹⁾	I _{IO} = 1 mA, T _A = 25°C	-5.5	-6.4	-7.5	V	
V_{HOLD}	Holding voltage ⁽²⁾	I _{IO} = 1 mA		5.8		V	
		I _{PP} = 1 A, TLP, from IO to GND		6.6			
V	Clamping voltage	I _{PP} = 5 A, TLP, from IO to GND	8.8		V		
V_{CLAMP}	Clamping Voltage	I _{PP} = 1 A, TLP, from GND to IO		6.6		v	
		I _{PP} = 5A, TLP, from GND to IO		8.8			
I _{LEAK}	Leakage current, any IO to GND	$V_{IO} = \pm 2.5 \text{ V}$			10	nA	
D	Dunamia vasiatanas	IO to GND		0.47		Ω	
R_{DYN}	Dynamic resistance	GND to IO		0.47			
C_L	Line capacitance	V_{IO} = 0 V, f = 1 MHz, IO to GND, T_A = 25°C		0.25	0.33	pF	
ΔC_L	Variation of line capacitance	Delta of capacitance between any two IO pins, $V_{IO} = 0$ V, $f = 1$ MHz, $T_A = 25$ °C, GND = 0 V		0.01	0.07	pF	
C _{CROSS}	Channel to channel capacitance	Capacitance from one IO to another, V _{IO} = 0 V, f = 1 MHz, GND = 0 V		0.13		pF	

⁽¹⁾ V_{BRF} and V_{BRR} are defined as the voltage when 1 mA is applied in the positive-going direction, before the device latches into the snapback state.

⁽²⁾ V_{HOLD} is defined as the voltage when 1 mA is applied in the negative-going direction, after the device has successfully latched into the snapback state.

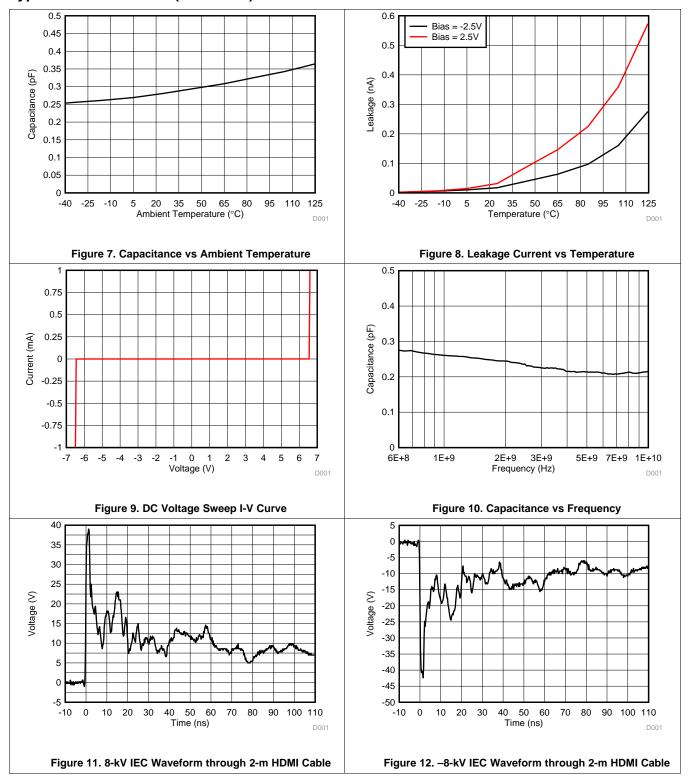


6.7 Typical Characteristics



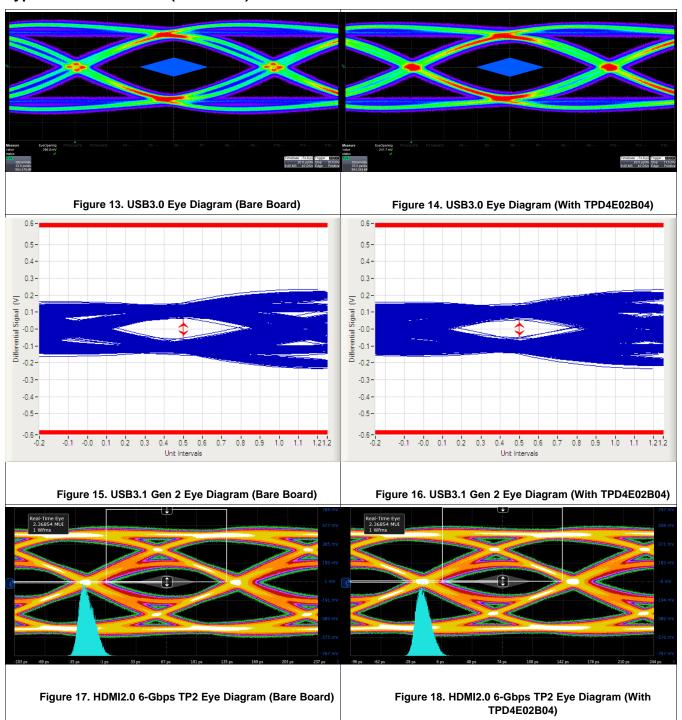


Typical Characteristics (continued)



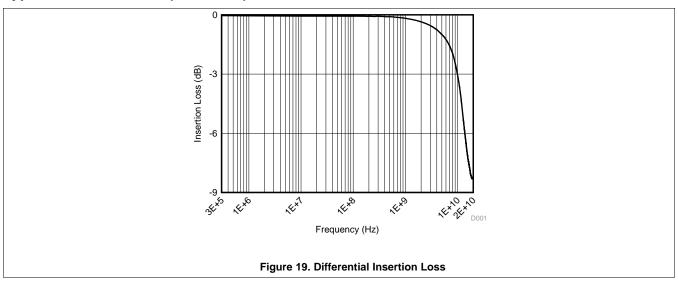


Typical Characteristics (continued)





Typical Characteristics (continued)



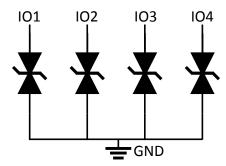


7 Detailed Description

7.1 Overview

The TPD4E02B04 is a bidirectional ESD Protection Diode with ultra-low capacitance. This device can dissipate ESD strikes above the maximum level specified by the IEC 61000-4-2 International Standard. The ultra-low capacitance makes this device ideal for protecting any super high-speed signal pins.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 IEC 61000-4-2 ESD Protection

The I/O pins can withstand ESD events up to ±12-kV contact and ±15-kV air gap. An ESD-surge clamp diverts the current to ground.

7.3.2 IEC 61000-4-4 EFT Protection

The I/O pins can withstand an electrical fast transient burst of up to 80 A (5/50 ns waveform, 4 kV with $50-\Omega$ impedance). An ESD-surge clamp diverts the current to ground.

7.3.3 IEC 61000-4-5 Surge Protection

The I/O pins can withstand surge events up to 2 A and 17 W (8/20 µs waveform). An ESD-surge clamp diverts this current to ground.

7.3.4 IO Capacitance

The capacitance between each I/O pin to ground is 0.25 pF (typical) and 0.33 pF (maximum). This device supports data rates up to 10 Gbps.

7.3.5 DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is a minimum of ± 5.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of ± 3.6 V.

7.3.6 Ultra Low Leakage Current

The I/O pins feature an ultra-low leakage current of 10 nA (maximum) with a bias of ±2.5 V.

7.3.7 Low ESD Clamping Voltage

The I/O pins feature an ESD clamp that is capable of clamping the voltage to 8.8 V (I_{PP} = 5 A).

7.3.8 Supports High Speed Interfaces

This device is capable of supporting high speed interfaces up to 10 Gbps, because of the extremely low IO capacitance.

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Feature Description (continued)

7.3.9 Industrial Temperature Range

This device features an industrial operating range of -40°C to +125°C.

7.3.10 Easy Flow-Through Routing Package

The layout of this device makes it simple and easy to add protection to an existing layout. The packages offers flow-through routing, requiring minimal modification to an existing layout.

7.4 Device Functional Modes

The TPD4E02B04 is a passive integrated circuit that triggers when voltages are above V_{BRF} or below V_{BRR} . During ESD events, voltages as high as ± 15 kV (air) can be directed to ground via the internal diode network. When the voltages on the protected line fall below the trigger levels of TPD4E02B04 (usually within 10s of nanoseconds) the device reverts to passive.



8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPD4E02B04 is a diode type TVS which is used to provide a path to ground for dissipating ESD events on high-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP} , to a safe level for the protected IC.

8.2 Typical Application

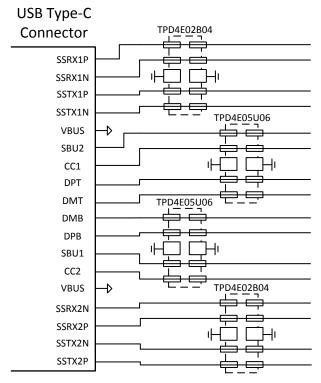


Figure 20. USB 3.1 Gen 2 Type-C ESD Schematic



Typical Application (continued)

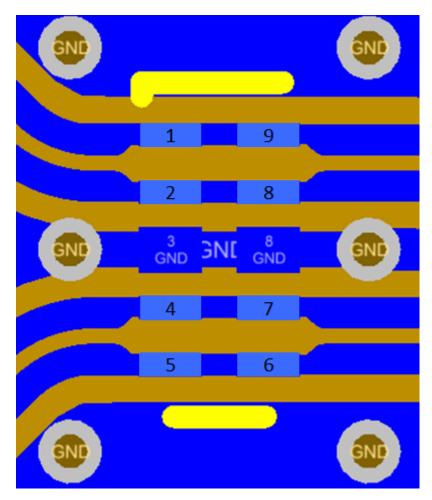


Figure 21. USB 3.1 Gen 2 SuperSpeed Layout

8.2.1 Design Requirements

For this design example two TPD4E02B04 devices and two TPD4E05U06 devices are being used in a USB 3.1 Gen 2 Type-C application. This provides a complete ESD protection scheme.

Given the USB 3.1 Gen 2 Type-C application, the parameters listed in Table 1 are known.

Table 1. Design Parameters

DESIGN PARAMETER	VALUE
Signal Range on SuperSpeed+ Lines	0 V to 3.6 V
Operating Frequency on SuperSpeed+ Lines	5 GHz
Signal Range on CC, SBU, and DP/DM Lines	0 V to 5 V
Operating Frequency on CC, SBU, and DP/DM Lines	up to 480 MHz



8.2.2 Detailed Design Procedure

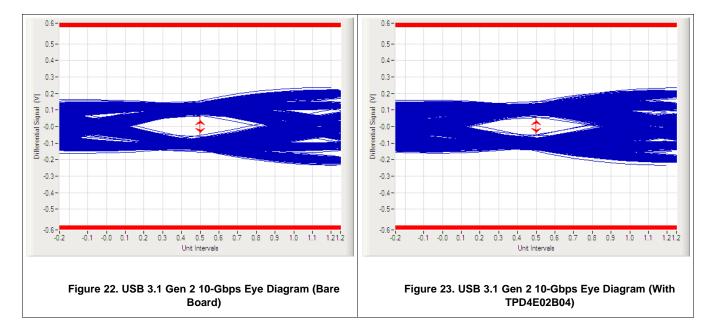
8.2.2.1 Signal Range

The TPD4E02B04 supports signal ranges between -3.6 V and 3.6 V, which supports the SuperSpeed+ pairs on the USB Type-C application. The TPD4E05U06 supports signal ranges between 0 V and 5.5 V, which supports the CC, SBU, and DP/DM lines.

8.2.2.2 Operating Frequency

The TPD4E02B04 has a 0.25 pF (typical) capacitance, which supports the USB3.1 Gen 2 data rates of 10 Gbps. The TPD4E05U06 has a 0.5 pF (typical) capacitance, which easily supports the CC, SBU, and DP/DM data rates.

8.2.3 Application Curves





9 Power Supply Recommendations

This device is a passive ESD device so there is no need to power it. Take care not to violate the recommended I/O specification (–3.6 V to 3.6 V) to ensure the device functions properly.

10 Layout

10.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
 - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
 - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
 - Electric fields tend to build up on corners, increasing EMI coupling.

10.2 Layout Examples

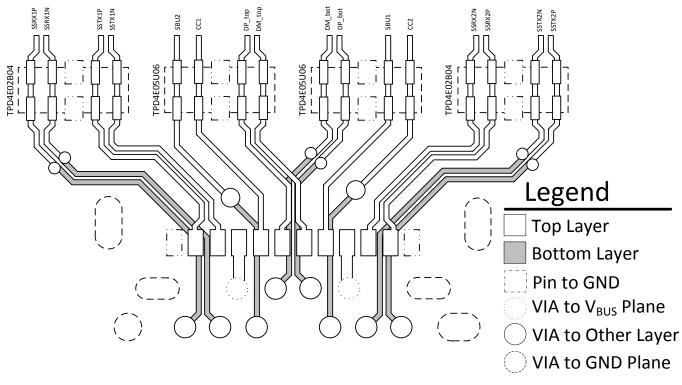


Figure 24. USB Type-C Mid-Mount, Hybrid Connector with One-Sided ESD Layout



Layout Examples (continued)

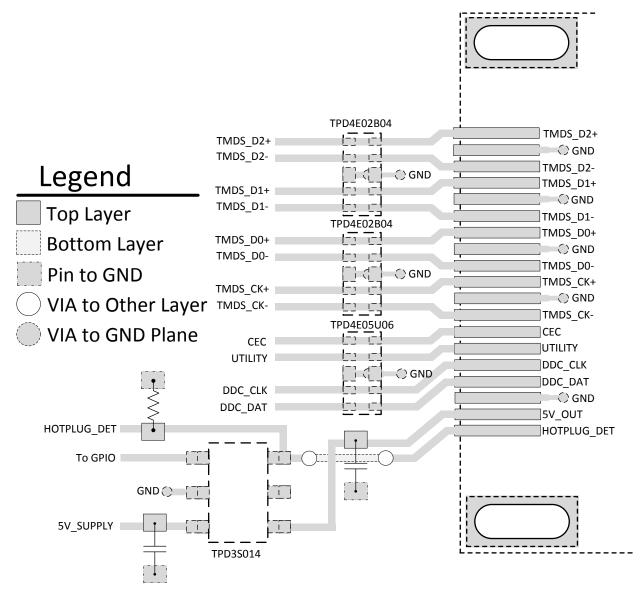


Figure 25. HDMI2.0 Type-A Transmitter Port Layout



11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- Reading and Understanding an ESD Protection Datasheet, SLLA305
- ESD Layout Guide, SLVA680
- Picking ESD Diodes for Ultra High-Speed Data Lines, SLVA785
- TPD4E02B04EVM Users Guide, SLVUAH6

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments.

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11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OPTION ADDENDUM



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPD4E02B04DQAR	ACTIVE	USON	DQA	10	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1SG 1SY	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM



10-Dec-2020

OTHER QUALIFIED VERSIONS OF TPD4E02B04:

Automotive: TPD4E02B04-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

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TAPE AND REEL INFORMATION

REEL DIMENSIONS Reel Diameter Reel Width (W1)



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

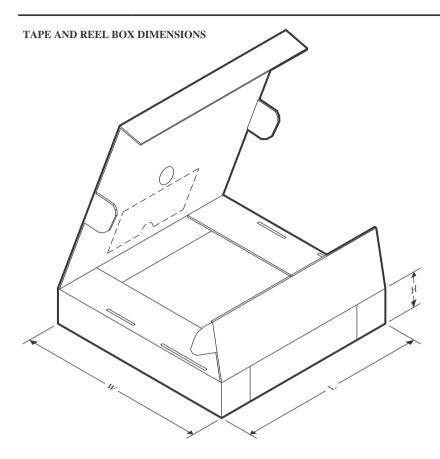
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD4E02B04DQAR	USON	DQA	10	3000	180.0	9.5	1.18	2.68	0.72	4.0	8.0	Q1

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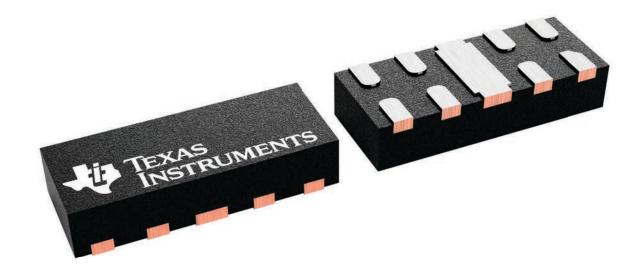
*All dimensions are nominal

Device F		Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPD4	4E02B04DQAR	USON	DQA	10	3000	189.0	185.0	36.0

1 x 2.5, 0.5 mm pitch

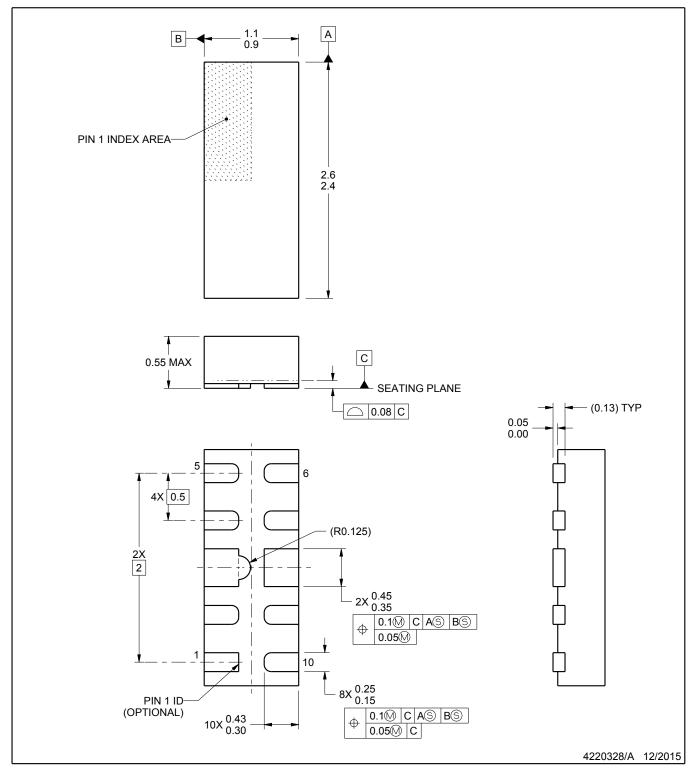
PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC SMALL OUTLINE - NO LEAD



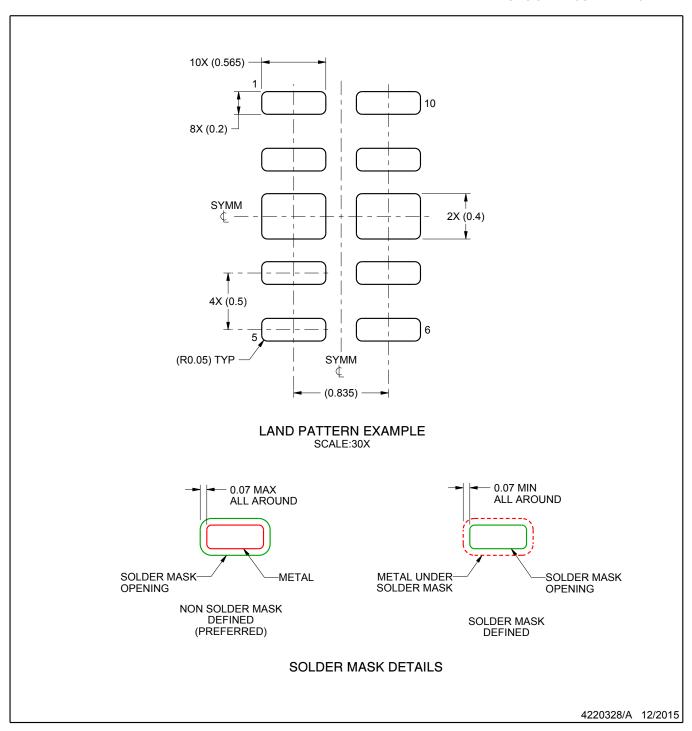
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



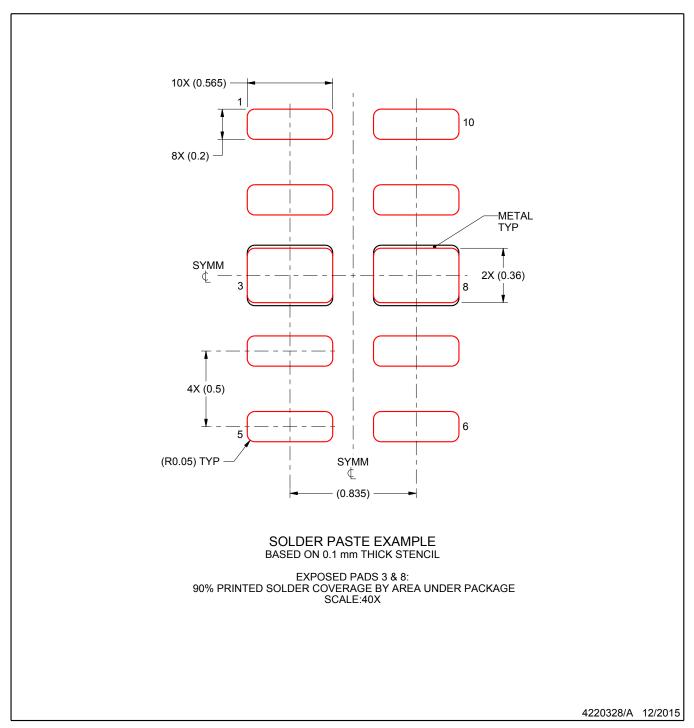
PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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